

a plurality of shunting interconnection lines, provided corresponding to the respective sub word lines in a second conductive layer formed under said first conductive layer, each shunting interconnection line for electrically connecting to a corresponding sub word line at a prescribed interval and allowing signal transmission between said each and said corresponding sub word line; and

a plurality of sub word drivers, provided corresponding to the sub word lines, each for driving a corresponding sub word line and a corresponding shunting interconnection line into a selected state according to at least a row select signal on a corresponding main word line.

Please add new claim 12 as follows:

-- 12. (New) The semiconductor memory device according to claim 1, wherein said plurality of shunting interconnecting lines are each electrically connected to the corresponding sub word line through contacts formed at said prescribed interval.--

REMARKS

Claims 1-12 are pending in this application with claims 3 and 8 withdrawn from consideration. By this Amendment, claim 1 is amended, and new claim 12 is added. Applicant does not disclaim any equivalent of any amended limitation. Reconsideration in view of the above amendments and the following remarks is respectfully requested.

The Office Action objects to the drawings under 37 C.F.R. §1.83(a) stating that "the metal interconnection line is a copper interconnection line must be shown or the feature(s) or canceled from the claim(s)." This rejection is respectfully traversed.

In particular, Applicant respectfully draws the Examiner's attention to Fig. 12, which shows shunting interconnection lines **72** deposited between insulating films **70** with the symbol